NSN 5962-01-351-9526

Memory Microcircuit - Page 1 of 2

Between 0.220 inches and 0.310 inches

Overall Height: 0.400 inches Body Length: 1.060 inches Body Width:



View Online at https://aerobasegroup.com/nsn/5962-01-351-9526

Body Height:
Between 0.130 inches and 0.185 inches
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Satellite communications terminal an/usc-3 (v) 1
Features Provided:
Hermetically sealed and burn in and monolithic and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
185.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
45.00 nanoseconds delay
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

NSN 5962-01-351-9526

Memory Microcircuit - Page 2 of 2



Terminal Type Ar	nd Quantity:
------------------	--------------

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

Fiig:

A458a0